

CLAIMS:

What is claimed is:

1. Apparatus for sensing neutron flow comprising:
a first substantially planar array of flash memory cells; and
5 a second substantially planar array of memory cells, the plane of the second substantially planar array of memory cells being at an angle relative to the plane of the first substantially planar array of memory cells.
- 10 2. The apparatus of claim 1 wherein at least one of the first and second substantially planar arrays is mounted on a neutron-absorbing substrate.
3. The apparatus of claim 1 wherein the first and second substantially planar arrays are mounted on neutron-absorbing substrates.
- 15 4. The apparatus of claim 1 wherein the angle between the plane of the first substantially planar array of memory cells and the plane of the second substantially planar array of memory cells is substantially 90°.
- 20 5. The apparatus of claim 1 and further comprising a third substantially planar array of memory cells, the plane of the third substantially planar array of memory cells being at an angle relative to the plane of the first substantially planar array of memory cells and being at an angle relative to the plane of the second substantially planar array of memory cells.
- 25 6. The apparatus of claim 5 wherein the angle between the plane of the first substantially planar array of memory cells and the plane of the second substantially planar array of memory cells is substantially 90°.
- 30 7. The apparatus of claim 5 wherein the angle between the plane of the first substantially planar array of memory cells and the plane of the second substantially planar array of memory cells is substantially 90°, and the angle between the plane of the second substantially planar array of memory cells and the plane of the third substantially planar array of memory cells is substantially 90°.
- 35 8. The apparatus of claim 7 wherein the angle between the plane of the first substantially planar array of memory cells and the plane of the third substantially planar array of memory cells is substantially 90°.

9. The apparatus of claim 8 wherein the memory cells are flash memory cells.

10. Apparatus for sensing neutron flow comprising:

a first substantially planar array of flash memory cells;

5 a second substantially planar array of flash memory cells having an edge adjacent an edge of the first substantially planar array of flash memory cells; and

a third substantially planar array of flash memory cells having a first edge adjacent an edge adjacent an edge of the first substantially planar array of flash memory cells and a second edge adjacent an edge of the second substantially planar array of flash memory cells;

10 the plane of the second substantially planar array of flash memory cells being at an angle relative to the plane of the first substantially planar array of flash memory cells;

the plane of the third substantially planar array of flash memory cells being at an angle relative to the plane of the first substantially planar array of flash memory cells and being at an angle relative to the plane of the second substantially planar array of flash memory cells.

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11. The apparatus of claim 10 wherein the first, second and third substantially planar arrays are mounted on neutron-absorbing substrates.

12. The apparatus of claim 11 wherein the angle between the plane of the first

20 substantially planar array of flash memory cells and the plane of the second substantially planar array of flash memory cells is substantially 90°.

13. The apparatus of claim 11 wherein the angle between the plane of the first

25 substantially planar array of flash memory cells and the plane of the second substantially planar array of flash memory cells is substantially 90°, and the angle between the plane of the second substantially planar array of flash memory cells and the plane of the third substantially planar array is substantially 90°.

14. The apparatus of claim 13 wherein the angle between the plane of the first

30 substantially planar array of flash memory cells and the plane of the third substantially planar array of flash memory cells is substantially 90°.

15. The apparatus of claim 14 wherein each of the first, second and third planar arrays of flash memory cells is substantially rectangular in configuration.

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